

















۰,





۰.









١.





| | scent 30 | |
|------------------------------|---------------------------|---|
| Type of Event | Spacecraft/ Instrument | Notes |
| Spontaneous Processor Resets | RHESSI | 3 events; all recoverable |
| a Startest | CLUSTER | Seen on some of 4 spacecraft; recoverable |
| | ChipSAT | S/C tumbled and required ground command to correct |
| High Bit Error Rates | GOES 9,10 | |
| Magnetic Torquers Disabled | GOES 9, 10, 12 | |
| Star Tracker Errors | MER | Excessive event counts |
| | MAP | Star Tracker Reset occurred |
| Read Errors | Stardust | Entered safe mode; recovered |
| Fallure? | Midori-2 | |
| Memory Errors | GENESIS | 19 errors on 19/29 |
| | Many | Increase in correctable error rates on solid- |

•

۰.

| Type of Event | Spacecraft/ | Notes |
|-----------------------|-----------------------|--|
| Instrument Failure | GOES-8 XRS | Under investigation as to cause |
| | Mars Odyssey/Marie | Under investigation as to cause; power consumption increase noted; S/C also had a safehold event – memory errors |
| | NOAA-17/AMSU-A1 | Lost scanner; under investigation |
| Excessive Count Rates | ACE, WIND | Plasma observations lost |
| | GALEX UV Detectors | Excess charge – turned off high voltages; Also Upset noted in instrument |
| | ACE | Solar Proton Detector saturated |
| Upset | Integral | Entered Safe mode |
| | POLAR/TIDE | Instrument reset spontaneously |
| Hot Pixels | SIRTFARAC | Increase in hot pixels on IR arrays; Proton heating also noted |
| Sale Mode | Nany | Many instruments were placed in Safe mode prior to or during the solar events for immediate |

Single Event Effects Specification (2 of 3)

2. Component SEU Specification

2.1 No SEE may cause permanent damage to a system or subsystem.

2.2 Electronic components shall be designed to be immune to SEE induced performance anomalies, or outages which require ground intervention to correct. Electronic component reliability shall be met in the SEU environment.

2.3 If a device is not immune to SEUs, analysis for SEU rates and effects must take place based on LET_e of the candidate devices as follows:

| | Device Threshold | Environment to be Assessed |
|---|--|--|
| | LET < 15" MeV"cm ² /mg | Cosmic Ray, Trapped Protons, Solar Proton Events |
| | LET, = 15*-100 MeV*cm²/mg | Galactic Cosmic Ray Heavy Ions, Solar Heavy Ions |
| | LET > 190 MeV*cm²/mg | No analysis required |
| 20 JR. 1888 R | transad mentan and managed to be up | ad for analysis is alway in Floures TRD. Both nominal and an |
| 2.5 Th particle 2.6 Th | i trapped proton environment to be us flux rates must be analyzed. e solar event environment to be used i | ed for analysis is given in Figures TBD. Both nominal and pe for analysis is given in Figure TBD. |
| 2.5 Th particle 2.6 Th 2.7 For be add | trapped proton environment to be us flux rates must be analyzed. a solar event environment to be used i any device that is not immune to SEL d to eliminate the possibility of dama | ed for analysis is given in Figures TBD. Both nominal and pa for analysis is given in Figure TBD. . or other potentially destructive conditions, protective circuitr ge and verified by analysis or test. |
| 2.5 Th particle 2.6 Th 2.7 For be add | trapped proton environment to be us flux rates must be analyzed. e solar event environment to be used i any device that is not immune to SEL d to eliminate the possibility of dama "This number is somewhat Some newer device | ed for analysis is given in Figures TBD. Both nominal and pa for analysis is given in Figure TBD. , or other potentially destructive conditions, protective circuitr ge and verified by analysis or test. arbitrary and is applicable to "standard" devices. es may require this number to be higher. |

| | | _ |
|--|--|----------------|
| NASA | Single Event Effects Specification | |
| | (3 of 3) | |
| 2. Compo | ment SEU Specification (Cont.) | |
| 2.8 For S error-critic Effect Crit level. | EU, the criticality of a device in it's specific application must be defined into one of three categories: cal, error-functional, or error-vulnerable. Please refer to the /radhome/papers/seecal.htm Single Event icality Analysis (SEECA) document for details. A SEECA analysis should be performed at the system | |
| 2.9 The in analysis o acceptable correction critical are | nproper operation caused by an SEU shall be reduced to acceptable levels. Systems engineering if circuit design, operating modes, duty cycle, device criticality etc. shall be used to determine a levels for that device. Means of gaining acceptable levels include part selection, error detection and ischemes, redundancy and voting methods, error tolerant coding, or acceptance of errors in non- tes. | |
| 2.10 A de | sign's resistance to SEE for the specified radiation environment must be demonstrated. | |
| 3. SEU G | and a finance | |
| Wherever LET _e > 10 | practical, procure SEE immune devices. SEE immune is defined as a device having an I MoV*cm*img. | |
| E device to recommen | net data doss not extet, ground testing is required. For commercial components, testing is ded on the Hight procursment lot. | |
| | EWRINE - Space Rediction Effects presented by Kenneth A. LaBel at Vitard de Lana - Mar 30.2004 | and the second |

NASA's Living With a Star (LWS) Space NASA Environment Testbed (SET) -A Dual Approach to Flight Validation Data mining Flight experiments Focus on correlating - The use of existing flight technology (semiconductor data to validate or develop to material) performance with improved models and solar-variant space tools environment (radiation, UV, Examples etc.) Model/technology validation and not device validation are - Linear device performance on the goals **Microelectronics and** In-situ environment **Photonics TestBed** monitoring allows for ground (MPTB) test protocol/model correlation Physics-based Solar **Multiple flight opportunities Array Degradation Tool** - Carrier under development (SAVANT) Investigations are selected via NASA Research Announcements (NRAs) or provided under partnering arrangements ce Radiation Effects presented by Kenneth A LaBel at Villard de Lans - Mar 30,200

